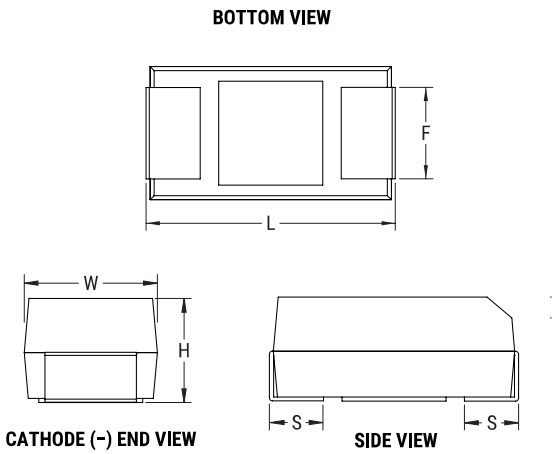
T555B756K075AT

T555, Tantalum, Polymer Tantalum, HRA, 75 uF, 10%, 75 VDC, N/A, 160 mOhms, 9.6 mm, 3 mm



Click here for the 3D model.

General Information	
Series	T555
Dielectric	Polymer Tantalum
Style	SMD Chip
RoHS	No
SCIP Number	43449f08-bd3e-4b72-a04c-6ca7dd4144ff
Termination	Tin
AEC-Q200	No
Typical Component Weight	5.54 g
Shelf Life	156 Weeks

Dimensions	
L	24.5mm +/-0.5mm
W	8.5mm +/-0.5mm
H	9.1mm +/-0.5mm
S	3mm +/-0.3mm
F	4.2mm +/-0.5mm

Packaging Specifications	
Packaging	Bulk, Box
Packaging Quantity	100

Specifications	
Capacitance	75 uF
Tolerance	10%
Voltage DC	75 VDC, 58.5 VDC (105°C), 86.25 VDC (85°C)
Temperature Range	-55/+105°C
Rated Temperature	85°C
Life	2000 Hrs
Dissipation Factor	6% (120Hz 25C)
Failure Rate	N/A
ESR	160 mOhm (100kHz 25C)
Ripple Current	1310 mAmps (40kHz 85C)
Leakage Current	42.2 uA (5min 25°C)
Testing and Reliability	25C +/-5C, 10 cycles, after constant voltage conditioning (KEMET standard)

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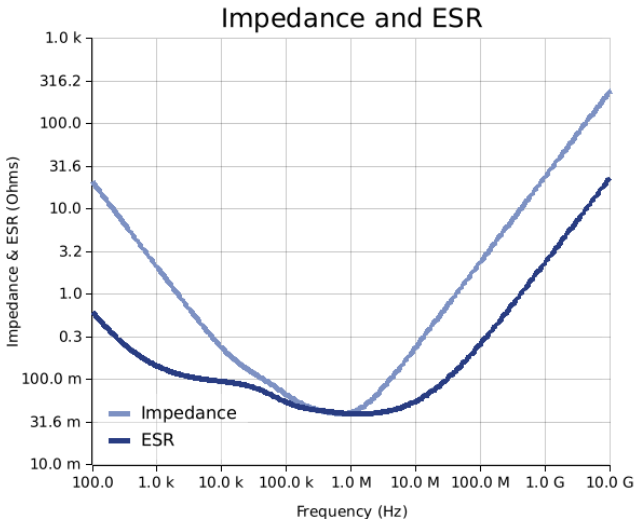
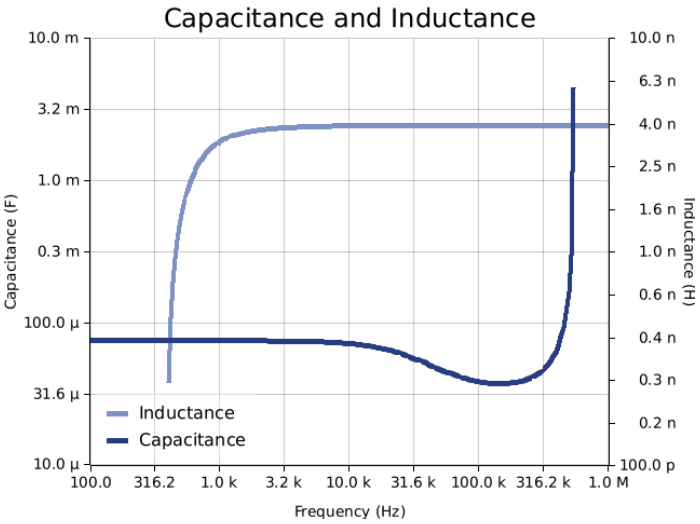
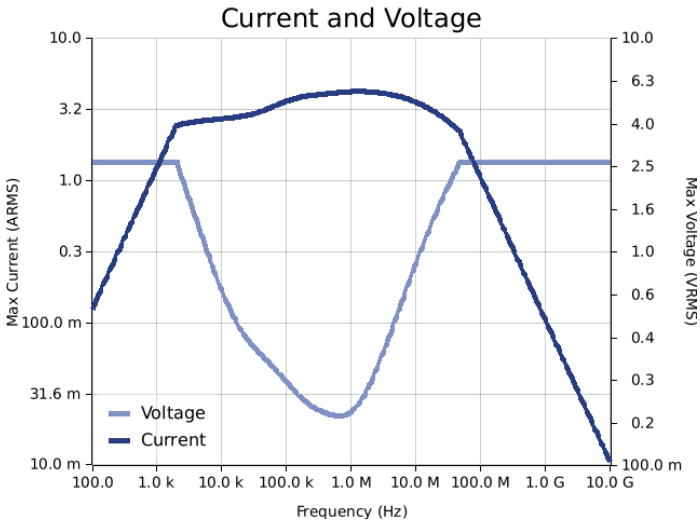
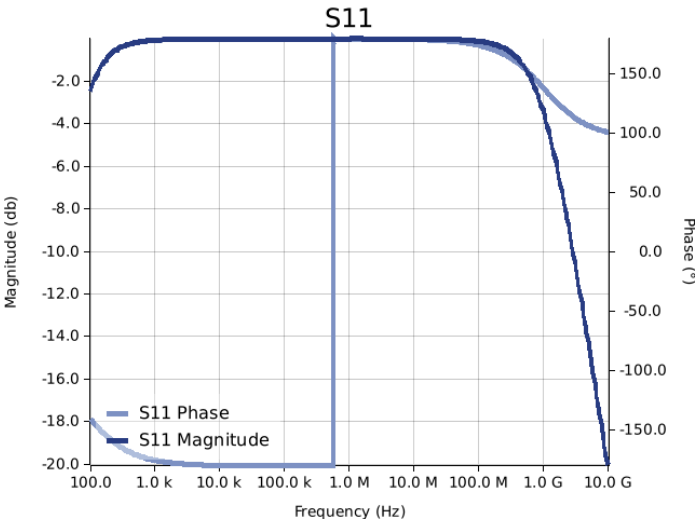
Simulations

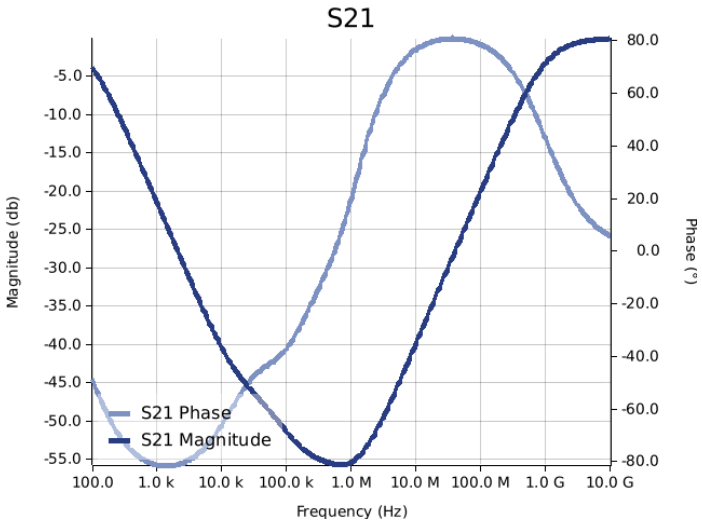
For the complete simulation environment please visit Y-SIM.











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These are simulations.
This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple “Ripple Current/Voltage vs. Frequency” plots is the ESR at ambient temperature.
- The ESR in the “Temperature Rise vs. Ripple Current” plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
- The effects shown herein are based on measured data from a multiple part sample of the parts in question.
- Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.
- The peak voltages generated in the “Temperature Rise vs. Combined Ripple Currents” plot are calculated for each frequency and are not combined with voltages generated at any other harmonics.
- Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the “Information”) are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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If you have any questions please contact K-SIM.